

ABSTRACT

In a semiconductor laser device (LD1), a semiconductor laser layer is formed on one face of a semiconductor substrate (1), and a p-type electrode (8) and an n-type electrode (11) are provided on the semiconductor laser layer side and the semiconductor substrate (1) side, respectively, so as to sandwich the semiconductor laser layer and the semiconductor substrate (1) therebetween. The p-type electrode (8) includes a first electrode (9) and a second electrode (10) that covers the first electrode (9).